

Appl. No. 09/902,056  
Amdt. dated October 28, 2003  
Reply to Office Action of August 27, 2003

Amendments to the Claims

Claims 10-18 (*Cancelled*)

26. (*Currently Amended*) A wafer, comprising:  
a substrate;

a porous layer comprised of a nanoporous material deposited with a dry process on the substrate, the porous layer including a low density portion closer to the substrate than a high density portion, the high density portion being a densified form of the low density portion, wherein the porous layer has a continuous range of density that decreases as the porous layer tends closer to the substrate; and

a cap layer deposited with a dry process on the porous layer in contact with the high density portion, the cap layer including an oxide-based material.

27. (*Previously Added*) The wafer of claim 26, wherein the cap layer includes a Plasma Enhanced Chemical Vapor Deposition (PECVD) oxide layer.

Claims 28-31 (*Cancelled*)

32. (*Currently Amended*) A device, comprising:

a wafer including a substrate; and

a layer of a nanoporous material deposited with a dry process on the substrate, the layer including a low density portion closer to the substrate than a high density portion, the high density portion being a densified form of the low density portion, wherein the nanoporous layer has a continuous range of density that decreases as the nanoporous layer tends closer to the substrate.

33. (*Previously Amended*) The device of claim 32, further comprising a cap layer deposited on the high density portion, the cap layer including an oxide-based material.

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34. *(Previously Amended)* The device of claim 33, wherein the cap layer includes a Plasma Enhanced Chemical Vapor Deposition (PECVD) oxide layer.

35. *(Previously Amended)* The device of claim 32, wherein the low density portion of the layer is in contact with the substrate.

36. *(Previously Amended)* The device of claim 32, wherein the layer is comprised of silicon dioxide.

Claims 37-40 *(Previously Withdrawn)*